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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

| | |
|--------------------------------|---------------------------------------------------------------------------------------------------------------------------------------|
| Product Status | Obsolete |
| Number of LABs/CLBs | 185000 |
| Number of Logic Elements/Cells | 490000 |
| Total RAM Bits | 41984000 |
| Number of I/O | 432 |
| Number of Gates | - |
| Voltage - Supply | 0.82V ~ 0.88V |
| Mounting Type | Surface Mount |
| Operating Temperature | 0°C ~ 85°C (TJ) |
| Package / Case | 1517-FBGA (40x40) |
| Supplier Device Package | 1517-FBGA (40x40) |
| Purchase URL | https://www.e-xfl.com/product-detail/intel/5sgxmb5r1f40c2ln |

Table 1. Stratix V GX and GS Commercial and Industrial Speed Grade Offering ^{(1), (2), (3)} (Part 2 of 2)

| Transceiver Speed Grade | Core Speed Grade | | | | | | | |
|--------------------------|------------------|---------|-----|-----|---------|---------|--------------------|-----|
| | C1 | C2, C2L | C3 | C4 | I2, I2L | I3, I3L | I3YY | I4 |
| 3 GX channel—8.5 Gbps | — | Yes | Yes | Yes | — | Yes | Yes ⁽⁴⁾ | Yes |

Notes to Table 1:

- (1) C = Commercial temperature grade; I = Industrial temperature grade.
 (2) Lower number refers to faster speed grade.
 (3) C2L, I2L, and I3L speed grades are for low-power devices.
 (4) I3YY speed grades can achieve up to 10.3125 Gbps.

Table 2 lists the industrial and commercial speed grades for the Stratix V GT devices.

Table 2. Stratix V GT Commercial and Industrial Speed Grade Offering ^{(1), (2)}

| Transceiver Speed Grade | Core Speed Grade | | | |
|----------------------------------------------------|------------------|-----|-----|-----|
| | C1 | C2 | I2 | I3 |
| 2 GX channel—12.5 Gbps GT channel—28.05 Gbps | Yes | Yes | — | — |
| 3 GX channel—12.5 Gbps GT channel—25.78 Gbps | Yes | Yes | Yes | Yes |

Notes to Table 2:

- (1) C = Commercial temperature grade; I = Industrial temperature grade.
 (2) Lower number refers to faster speed grade.

Absolute Maximum Ratings

Absolute maximum ratings define the maximum operating conditions for Stratix V devices. The values are based on experiments conducted with the devices and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied for these conditions.



Conditions other than those listed in Table 3 may cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse effects on the device.

Table 3. Absolute Maximum Ratings for Stratix V Devices (Part 1 of 2)

| Symbol | Description | Minimum | Maximum | Unit |
|---------------------|------------------------------------------------------------------------|---------|---------|------|
| V _{CC} | Power supply for core voltage and periphery circuitry | −0.5 | 1.35 | V |
| V _{CCPT} | Power supply for programmable power technology | −0.5 | 1.8 | V |
| V _{CCPGM} | Power supply for configuration pins | −0.5 | 3.9 | V |
| V _{CC_AUX} | Auxiliary supply for the programmable power technology | −0.5 | 3.4 | V |
| V _{CCBAT} | Battery back-up power supply for design security volatile key register | −0.5 | 3.9 | V |
| V _{CCPD} | I/O pre-driver power supply | −0.5 | 3.9 | V |
| V _{CCIO} | I/O power supply | −0.5 | 3.9 | V |

Table 5 lists the maximum allowed input overshoot voltage and the duration of the overshoot voltage as a percentage of device lifetime. The maximum allowed overshoot duration is specified as a percentage of high time over the lifetime of the device. A DC signal is equivalent to 100% of the duty cycle. For example, a signal that overshoots to 3.95 V can be at 3.95 V for only ~21% over the lifetime of the device; for a device lifetime of 10 years, the overshoot duration amounts to ~2 years.

Table 5. Maximum Allowed Overshoot During Transitions

| Symbol | Description | Condition (V) | Overshoot Duration as % @ $T_J = 100^\circ\text{C}$ | Unit |
|------------|------------------|---------------|--------------------------------------------------------|------|
| V_i (AC) | AC input voltage | 3.8 | 100 | % |
| | | 3.85 | 64 | % |
| | | 3.9 | 36 | % |
| | | 3.95 | 21 | % |
| | | 4 | 12 | % |
| | | 4.05 | 7 | % |
| | | 4.1 | 4 | % |
| | | 4.15 | 2 | % |
| | | 4.2 | 1 | % |

Figure 1. Stratix V Device Overshoot Duration



I/O Pin Leakage Current

Table 9 lists the Stratix V I/O pin leakage current specifications.

Table 9. I/O Pin Leakage Current for Stratix V Devices ⁽¹⁾

| Symbol | Description | Conditions | Min | Typ | Max | Unit |
|----------|--------------------|--------------------------------------------|-----|-----|-----|---------------|
| I_I | Input pin | $V_I = 0 \text{ V to } V_{CCIO\text{MAX}}$ | -30 | — | 30 | μA |
| I_{OZ} | Tri-stated I/O pin | $V_O = 0 \text{ V to } V_{CCIO\text{MAX}}$ | -30 | — | 30 | μA |

Note to Table 9:

(1) If $V_O = V_{CCIO}$ to $V_{CCIO\text{MAX}}$, 100 μA of leakage current per I/O is expected.

Bus Hold Specifications

Table 10 lists the Stratix V device family bus hold specifications.

Table 10. Bus Hold Parameters for Stratix V Devices

| Parameter | Symbol | Conditions | V _{CCIO} | | | | | | | | | | Unit |
|-------------------------|-------------------|------------------------------------------------|-------------------|------|-------|------|-------|------|-------|------|-------|------|------|
| | | | 1.2 V | | 1.5 V | | 1.8 V | | 2.5 V | | 3.0 V | | |
| | | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | |
| Low sustaining current | I _{SUSL} | V _{IN} > V _{IL} (maximum) | 22.5 | — | 25.0 | — | 30.0 | — | 50.0 | — | 70.0 | — | μA |
| High sustaining current | I _{SUSH} | V _{IN} < V _{IH} (minimum) | −22.5 | — | −25.0 | — | −30.0 | — | −50.0 | — | −70.0 | — | μA |
| Low overdrive current | I _{ODL} | 0V < V _{IN} < V _{CCIO} | — | 120 | — | 160 | — | 200 | — | 300 | — | 500 | μA |
| High overdrive current | I _{ODH} | 0V < V _{IN} < V _{CCIO} | — | −120 | — | −160 | — | −200 | — | −300 | — | −500 | μA |
| Bus-hold trip point | V _{TRIP} | — | 0.45 | 0.95 | 0.50 | 1.00 | 0.68 | 1.07 | 0.70 | 1.70 | 0.80 | 2.00 | V |

On-Chip Termination (OCT) Specifications

If you enable OCT calibration, calibration is automatically performed at power-up for I/Os connected to the calibration block. Table 11 lists the Stratix V OCT termination calibration accuracy specifications.

Table 11. OCT Calibration Accuracy Specifications for Stratix V Devices ⁽¹⁾ (Part 1 of 2)

| Symbol | Description | Conditions | Calibration Accuracy | | | | Unit |
|--------------------|---------------------------------------------------------------------|-------------------------------------------------------|----------------------|----------|----------------|----------|------|
| | | | C1 | C2,I2 | C3,I3, I3YY | C4,I4 | |
| 25- Ω R_S | Internal series termination with calibration (25- Ω setting) | $V_{\text{CCIO}} = 3.0, 2.5, 1.8, 1.5, 1.2 \text{ V}$ | ± 15 | ± 15 | ± 15 | ± 15 | % |

Table 12. OCT Without Calibration Resistance Tolerance Specifications for Stratix V Devices (Part 2 of 2)

| Symbol | Description | Conditions | Resistance Tolerance | | | | Unit |
|----------------------|----------------------------------------------------------------|-----------------------------------|----------------------|--------|--------------|--------|------|
| | | | C1 | C2, I2 | C3, I3, I3YY | C4, I4 | |
| 50-Ω R _S | Internal series termination without calibration (50-Ω setting) | V _{CCIO} = 1.8 and 1.5 V | ±30 | ±30 | ±40 | ±40 | % |
| 50-Ω R _S | Internal series termination without calibration (50-Ω setting) | V _{CCIO} = 1.2 V | ±35 | ±35 | ±50 | ±50 | % |
| 100-Ω R _D | Internal differential termination (100-Ω setting) | V _{CCPD} = 2.5 V | ±25 | ±25 | ±25 | ±25 | % |

Calibration accuracy for the calibrated series and parallel OCTs are applicable at the moment of calibration. When voltage and temperature conditions change after calibration, the tolerance may change.

OCT calibration is automatically performed at power-up for OCT-enabled I/Os. Table 13 lists the OCT variation with temperature and voltage after power-up calibration. Use Table 13 to determine the OCT variation after power-up calibration and Equation 1 to determine the OCT variation without recalibration.

Equation 1. OCT Variation Without Recalibration for Stratix V Devices ^{(1), (2), (3), (4), (5), (6)}

$$R_{OCT} = R_{SCAL} \left(1 + \left\langle \frac{dR}{dT} \times \Delta T \right\rangle \pm \left\langle \frac{dR}{dV} \times \Delta V \right\rangle \right)$$

Notes to Equation 1:

- (1) The R_{OCT} value shows the range of OCT resistance with the variation of temperature and V_{CCIO}.
- (2) R_{SCAL} is the OCT resistance value at power-up.
- (3) ΔT is the variation of temperature with respect to the temperature at power-up.
- (4) ΔV is the variation of voltage with respect to the V_{CCIO} at power-up.
- (5) dR/dT is the percentage change of R_{SCAL} with temperature.
- (6) dR/dV is the percentage change of R_{SCAL} with voltage.

Table 13 lists the on-chip termination variation after power-up calibration.

Table 13. OCT Variation after Power-Up Calibration for Stratix V Devices (Part 1 of 2) ⁽¹⁾

| Symbol | Description | V _{CCIO} (V) | Typical | Unit |
|--------|--------------------------------------------------|-----------------------|---------|--------|
| dR/dV | OCT variation with voltage without recalibration | 3.0 | 0.0297 | % / mV |
| | | 2.5 | 0.0344 | |
| | | 1.8 | 0.0499 | |
| | | 1.5 | 0.0744 | |
| | | 1.2 | 0.1241 | |

Table 19. Single-Ended SSTL, HSTL, and HSUL I/O Standards Signal Specifications for Stratix V Devices (Part 2 of 2)

| I/O Standard | $V_{IL(DC)} (V)$ | | $V_{IH(DC)} (V)$ | | $V_{IL(AC)} (V)$ | $V_{IH(AC)} (V)$ | $V_{OL} (V)$ | $V_{OH} (V)$ | $I_{ol} (mA)$ | $I_{oh} (mA)$ |
|------------------|------------------|------------------|------------------|-------------------|------------------|------------------|-------------------|-------------------|---------------|---------------|
| | Min | Max | Min | Max | Max | Min | Max | Min | | |
| HSTL-18 Class I | — | $V_{REF} - 0.1$ | $V_{REF} + 0.1$ | — | $V_{REF} - 0.2$ | $V_{REF} + 0.2$ | 0.4 | $V_{CCIO} - 0.4$ | 8 | -8 |
| HSTL-18 Class II | — | $V_{REF} - 0.1$ | $V_{REF} + 0.1$ | — | $V_{REF} - 0.2$ | $V_{REF} + 0.2$ | 0.4 | $V_{CCIO} - 0.4$ | 16 | -16 |
| HSTL-15 Class I | — | $V_{REF} - 0.1$ | $V_{REF} + 0.1$ | — | $V_{REF} - 0.2$ | $V_{REF} + 0.2$ | 0.4 | $V_{CCIO} - 0.4$ | 8 | -8 |
| HSTL-15 Class II | — | $V_{REF} - 0.1$ | $V_{REF} + 0.1$ | — | $V_{REF} - 0.2$ | $V_{REF} + 0.2$ | 0.4 | $V_{CCIO} - 0.4$ | 16 | -16 |
| HSTL-12 Class I | -0.15 | $V_{REF} - 0.08$ | $V_{REF} + 0.08$ | $V_{CCIO} + 0.15$ | $V_{REF} - 0.15$ | $V_{REF} + 0.15$ | $0.25^* V_{CCIO}$ | $0.75^* V_{CCIO}$ | 8 | -8 |
| HSTL-12 Class II | -0.15 | $V_{REF} - 0.08$ | $V_{REF} + 0.08$ | $V_{CCIO} + 0.15$ | $V_{REF} - 0.15$ | $V_{REF} + 0.15$ | $0.25^* V_{CCIO}$ | $0.75^* V_{CCIO}$ | 16 | -16 |
| HSUL-12 | — | $V_{REF} - 0.13$ | $V_{REF} + 0.13$ | — | $V_{REF} - 0.22$ | $V_{REF} + 0.22$ | $0.1^* V_{CCIO}$ | $0.9^* V_{CCIO}$ | — | — |

Table 20. Differential SSTL I/O Standards for Stratix V Devices

| I/O Standard | $V_{CCIO} (V)$ | | | $V_{SWING(DC)} (V)$ | | $V_{X(AC)} (V)$ | | | $V_{SWING(AC)} (V)$ | |
|----------------------|----------------|------|-------|---------------------|------------------|----------------------|--------------|----------------------|---------------------------|---------------------------|
| | Min | Typ | Max | Min | Max | Min | Typ | Max | Min | Max |
| SSTL-2 Class I, II | 2.375 | 2.5 | 2.625 | 0.3 | $V_{CCIO} + 0.6$ | $V_{CCIO}/2 - 0.2$ | — | $V_{CCIO}/2 + 0.2$ | 0.62 | $V_{CCIO} + 0.6$ |
| SSTL-18 Class I, II | 1.71 | 1.8 | 1.89 | 0.25 | $V_{CCIO} + 0.6$ | $V_{CCIO}/2 - 0.175$ | — | $V_{CCIO}/2 + 0.175$ | 0.5 | $V_{CCIO} + 0.6$ |
| SSTL-15 Class I, II | 1.425 | 1.5 | 1.575 | 0.2 | (1) | $V_{CCIO}/2 - 0.15$ | — | $V_{CCIO}/2 + 0.15$ | 0.35 | — |
| SSTL-135 Class I, II | 1.283 | 1.35 | 1.45 | 0.2 | (1) | $V_{CCIO}/2 - 0.15$ | $V_{CCIO}/2$ | $V_{CCIO}/2 + 0.15$ | $2(V_{IH(AC)} - V_{REF})$ | $2(V_{IL(AC)} - V_{REF})$ |
| SSTL-125 Class I, II | 1.19 | 1.25 | 1.31 | 0.18 | (1) | $V_{CCIO}/2 - 0.15$ | $V_{CCIO}/2$ | $V_{CCIO}/2 + 0.15$ | $2(V_{IH(AC)} - V_{REF})$ | — |
| SSTL-12 Class I, II | 1.14 | 1.2 | 1.26 | 0.18 | — | $V_{REF} - 0.15$ | $V_{CCIO}/2$ | $V_{REF} + 0.15$ | -0.30 | 0.30 |

Note to Table 20:

(1) The maximum value for $V_{SWING(DC)}$ is not defined. However, each single-ended signal needs to be within the respective single-ended limits ($V_{IH(DC)}$ and $V_{IL(DC)}$).

Table 21. Differential HSTL and HSUL I/O Standards for Stratix V Devices (Part 1 of 2)

| I/O Standard | $V_{CCIO} (V)$ | | | $V_{DIF(DC)} (V)$ | | $V_{X(AC)} (V)$ | | | $V_{CM(DC)} (V)$ | | | $V_{DIF(AC)} (V)$ | |
|---------------------|----------------|-----|-------|-------------------|-----|-----------------|-----|------|------------------|-----|------|-------------------|-----|
| | Min | Typ | Max | Min | Max | Min | Typ | Max | Min | Typ | Max | Min | Max |
| HSTL-18 Class I, II | 1.71 | 1.8 | 1.89 | 0.2 | — | 0.78 | — | 1.12 | 0.78 | — | 1.12 | 0.4 | — |
| HSTL-15 Class I, II | 1.425 | 1.5 | 1.575 | 0.2 | — | 0.68 | — | 0.9 | 0.68 | — | 0.9 | 0.4 | — |

Table 23. Transceiver Specifications for Stratix V GX and GS Devices ⁽¹⁾ (Part 4 of 7)

| Symbol/ Description | Conditions | Transceiver Speed Grade 1 | | | Transceiver Speed Grade 2 | | | Transceiver Speed Grade 3 | | | Unit |
|------------------------------------------------------------|---------------------------------------------------------|------------------------------|-----------|-----|------------------------------|-----------|-----|------------------------------|-----------|-----|------|
| | | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max | |
| Differential on-chip termination resistors ⁽²¹⁾ | 85-Ω setting | — | 85 ± 30% | — | — | 85 ± 30% | — | — | 85 ± 30% | — | Ω |
| | 100-Ω setting | — | 100 ± 30% | — | — | 100 ± 30% | — | — | 100 ± 30% | — | Ω |
| | 120-Ω setting | — | 120 ± 30% | — | — | 120 ± 30% | — | — | 120 ± 30% | — | Ω |
| | 150-Ω setting | — | 150 ± 30% | — | — | 150 ± 30% | — | — | 150 ± 30% | — | Ω |
| V _{ICM} (AC and DC coupled) | V _{CCR_GXB} = 0.85 V or 0.9 V full bandwidth | — | 600 | — | — | 600 | — | — | 600 | — | mV |
| | V _{CCR_GXB} = 0.85 V or 0.9 V half bandwidth | — | 600 | — | — | 600 | — | — | 600 | — | mV |
| | V _{CCR_GXB} = 1.0 V/1.05 V full bandwidth | — | 700 | — | — | 700 | — | — | 700 | — | mV |
| | V _{CCR_GXB} = 1.0 V half bandwidth | — | 750 | — | — | 750 | — | — | 750 | — | mV |
| t _{LTR} ⁽¹¹⁾ | — | — | — | 10 | — | — | 10 | — | — | 10 | μs |
| t _{LTD} ⁽¹²⁾ | — | 4 | — | — | 4 | — | — | 4 | — | — | μs |
| t _{LTD_manual} ⁽¹³⁾ | — | 4 | — | — | 4 | — | — | 4 | — | — | μs |
| t _{LTR_LTD_manual} ⁽¹⁴⁾ | — | 15 | — | — | 15 | — | — | 15 | — | — | μs |
| Run Length | — | — | — | 200 | — | — | 200 | — | — | 200 | UI |
| Programmable equalization (AC Gain) ⁽¹⁰⁾ | Full bandwidth (6.25 GHz) Half bandwidth (3.125 GHz) | — | — | 16 | — | — | 16 | — | — | 16 | dB |

Table 28. Transceiver Specifications for Stratix V GT Devices (Part 1 of 5) ⁽¹⁾

| Symbol/ Description | Conditions | Transceiver Speed Grade 2 | | | Transceiver Speed Grade 3 | | | Unit |
|----------------------------------------------------------------|--------------------------------------------------------|----------------------------------------------------------------------------------------|-----------|------|------------------------------|-----------|------|------|
| | | Min | Typ | Max | Min | Typ | Max | |
| Reference Clock | | | | | | | | |
| Supported I/O Standards | Dedicated reference clock pin | 1.2-V PCML, 1.4-V PCML, 1.5-V PCML, 2.5-V PCML, Differential LVPECL, LVDS, and HCSL | | | | | | |
| | RX reference clock pin | 1.4-V PCML, 1.5-V PCML, 2.5-V PCML, LVPECL, and LVDS | | | | | | |
| Input Reference Clock Frequency (CMU PLL) ⁽⁶⁾ | — | 40 | — | 710 | 40 | — | 710 | MHz |
| Input Reference Clock Frequency (ATX PLL) ⁽⁶⁾ | — | 100 | — | 710 | 100 | — | 710 | MHz |
| Rise time | 20% to 80% | — | — | 400 | — | — | 400 | ps |
| Fall time | 80% to 20% | — | — | 400 | — | — | 400 | |
| Duty cycle | — | 45 | — | 55 | 45 | — | 55 | % |
| Spread-spectrum modulating clock frequency | PCI Express (PCIe) | 30 | — | 33 | 30 | — | 33 | kHz |
| Spread-spectrum downspread | PCIe | — | 0 to −0.5 | — | — | 0 to −0.5 | — | % |
| On-chip termination resistors ⁽¹⁹⁾ | — | — | 100 | — | — | 100 | — | Ω |
| Absolute V _{MAX} ⁽³⁾ | Dedicated reference clock pin | — | — | 1.6 | — | — | 1.6 | V |
| | RX reference clock pin | — | — | 1.2 | — | — | 1.2 | |
| Absolute V _{MIN} | — | -0.4 | — | — | -0.4 | — | — | V |
| Peak-to-peak differential input voltage | — | 200 | — | 1600 | 200 | — | 1600 | mV |
| V _{ICM} (AC coupled) | Dedicated reference clock pin | 1050/1000 ⁽²⁾ | | | 1050/1000 ⁽²⁾ | | | mV |
| | RX reference clock pin | 1.0/0.9/0.85 ⁽²²⁾ | | | 1.0/0.9/0.85 ⁽²²⁾ | | | V |
| V _{ICM} (DC coupled) | HCSL I/O standard for PCIe reference clock | 250 | — | 550 | 250 | — | 550 | mV |

Table 28. Transceiver Specifications for Stratix V GT Devices (Part 3 of 5) ⁽¹⁾

| Symbol/ Description | Conditions | Transceiver Speed Grade 2 | | | Transceiver Speed Grade 3 | | | Unit |
|----------------------------------------------------------------------------|---------------------------------|------------------------------|---------------|--------|------------------------------|---------------|--------|-----------|
| | | Min | Typ | Max | Min | Typ | Max | |
| Differential on-chip termination resistors ⁽⁷⁾ | GT channels | — | 100 | — | — | 100 | — | Ω |
| Differential on-chip termination resistors for GX channels ⁽¹⁹⁾ | 85- Ω setting | — | 85 \pm 30% | — | — | 85 \pm 30% | — | Ω |
| | 100- Ω setting | — | 100 \pm 30% | — | — | 100 \pm 30% | — | Ω |
| | 120- Ω setting | — | 120 \pm 30% | — | — | 120 \pm 30% | — | Ω |
| | 150- Ω setting | — | 150 \pm 30% | — | — | 150 \pm 30% | — | Ω |
| V _{ICM} (AC coupled) | GT channels | — | 650 | — | — | 650 | — | mV |
| VICM (AC and DC coupled) for GX Channels | VCCR_GXB = 0.85 V or 0.9 V | — | 600 | — | — | 600 | — | mV |
| | VCCR_GXB = 1.0 V full bandwidth | — | 700 | — | — | 700 | — | mV |
| | VCCR_GXB = 1.0 V half bandwidth | — | 750 | — | — | 750 | — | mV |
| t _{LTR} ⁽⁹⁾ | — | — | — | 10 | — | — | 10 | μ s |
| t _{LTD} ⁽¹⁰⁾ | — | 4 | — | — | 4 | — | — | μ s |
| t _{LTD_manual} ⁽¹¹⁾ | — | 4 | — | — | 4 | — | — | μ s |
| t _{LTR_LTD_manual} ⁽¹²⁾ | — | 15 | — | — | 15 | — | — | μ s |
| Run Length | GT channels | — | — | 72 | — | — | 72 | CID |
| | GX channels | ⁽⁸⁾ | | | | | | |
| CDR PPM | GT channels | — | — | 1000 | — | — | 1000 | \pm PPM |
| | GX channels | ⁽⁸⁾ | | | | | | |
| Programmable equalization (AC Gain) ⁽⁵⁾ | GT channels | — | — | 14 | — | — | 14 | dB |
| | GX channels | ⁽⁸⁾ | | | | | | |
| Programmable DC gain ⁽⁶⁾ | GT channels | — | — | 7.5 | — | — | 7.5 | dB |
| | GX channels | ⁽⁸⁾ | | | | | | |
| Differential on-chip termination resistors ⁽⁷⁾ | GT channels | — | 100 | — | — | 100 | — | Ω |
| Transmitter | | | | | | | | |
| Supported I/O Standards | — | 1.4-V and 1.5-V PCML | | | | | | |
| Data rate (Standard PCS) | GX channels | 600 | — | 8500 | 600 | — | 8500 | Mbps |
| Data rate (10G PCS) | GX channels | 600 | — | 12,500 | 600 | — | 12,500 | Mbps |

Figure 4 shows the differential transmitter output waveform.

Figure 4. Differential Transmitter/Receiver Output/Input Waveform



Figure 5 shows the Stratix V AC gain curves for GT channels.

Figure 5. AC Gain Curves for GT Channels

Table 33. Memory Block Performance Specifications for Stratix V Devices ^{(1), (2)} (Part 2 of 2)

| Memory | Mode | Resources Used | | Performance | | | | | | | Unit |
|------------|--------------------------------------------------------------------------------------------------|----------------|--------|-------------|---------|-----|-----|---------|---------------|-----|------|
| | | ALUTs | Memory | C1 | C2, C2L | C3 | C4 | I2, I2L | I3, I3L, I3YY | I4 | |
| M20K Block | Single-port, all supported widths | 0 | 1 | 700 | 700 | 650 | 550 | 700 | 500 | 450 | MHz |
| | Simple dual-port, all supported widths | 0 | 1 | 700 | 700 | 650 | 550 | 700 | 500 | 450 | MHz |
| | Simple dual-port with the read-during-write option set to Old Data , all supported widths | 0 | 1 | 525 | 525 | 455 | 400 | 525 | 455 | 400 | MHz |
| | Simple dual-port with ECC enabled, 512 × 32 | 0 | 1 | 450 | 450 | 400 | 350 | 450 | 400 | 350 | MHz |
| | Simple dual-port with ECC and optional pipeline registers enabled, 512 × 32 | 0 | 1 | 600 | 600 | 500 | 450 | 600 | 500 | 450 | MHz |
| | True dual port, all supported widths | 0 | 1 | 700 | 700 | 650 | 550 | 700 | 500 | 450 | MHz |
| | ROM, all supported widths | 0 | 1 | 700 | 700 | 650 | 550 | 700 | 500 | 450 | MHz |

Notes to Table 33:

- (1) To achieve the maximum memory block performance, use a memory block clock that comes through global clock routing from an on-chip PLL set to **50%** output duty cycle. Use the Quartus II software to report timing for this and other memory block clocking schemes.
- (2) When you use the error detection cyclical redundancy check (CRC) feature, there is no degradation in F_{MAX}.
- (3) The F_{MAX} specification is only achievable with Fitter options, **MLAB Implementation In 16-Bit Deep Mode** enabled.

Temperature Sensing Diode Specifications

Table 34 lists the internal TSD specification.

Table 34. Internal Temperature Sensing Diode Specification

| Temperature Range | Accuracy | Offset Calibrated Option | Sampling Rate | Conversion Time | Resolution | Minimum Resolution with no Missing Codes |
|-------------------|----------|--------------------------|----------------|-----------------|------------|------------------------------------------|
| –40°C to 100°C | ±8°C | No | 1 MHz, 500 KHz | < 100 ms | 8 bits | 8 bits |

Table 35 lists the specifications for the Stratix V external temperature sensing diode.

Table 35. External Temperature Sensing Diode Specifications for Stratix V Devices

| Description | Min | Typ | Max | Unit |
|------------------------------------------|-------|-------|-------|------|
| I _{bias} , diode source current | 8 | — | 200 | μA |
| V _{bias} , voltage across diode | 0.3 | — | 0.9 | V |
| Series resistance | — | — | < 1 | Ω |
| Diode ideality factor | 1.006 | 1.008 | 1.010 | — |

Periphery Performance

This section describes periphery performance, including high-speed I/O and external memory interface.

I/O performance supports several system interfaces, such as the **LVDS** high-speed I/O interface, external memory interface, and the **PCI/PCI-X** bus interface.

General-purpose I/O standards such as 3.3-, 2.5-, 1.8-, and 1.5-**LVTTL/LVCMOS** are capable of a typical 167 MHz and 1.2-**LVCMOS** at 100 MHz interfacing frequency with a 10 pF load.



The actual achievable frequency depends on design- and system-specific factors. Ensure proper timing closure in your design and perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specification

Table 36 lists high-speed I/O timing for Stratix V devices.

Table 36. High-Speed I/O Specifications for Stratix V Devices ⁽¹⁾, ⁽²⁾ (Part 1 of 4)

| Symbol | Conditions | C1 | | | C2, C2L, I2, I2L | | | C3, I3, I3L, I3YY | | | C4,I4 | | | Unit |
|--------------------------------------------------------------------------------------------|----------------------------------------------------|-----|-----|-----|------------------|-----|-----|-------------------|-----|--------------------|-------|-----|--------------------|------|
| | | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max | |
| $f_{\text{HCLK_in}}$ (input clock frequency) True Differential I/O Standards | Clock boost factor $W = 1$ to 40 ⁽⁴⁾ | 5 | — | 800 | 5 | — | 800 | 5 | — | 625 | 5 | — | 525 | MHz |
| $f_{\text{HCLK_in}}$ (input clock frequency) Single Ended I/O Standards ⁽³⁾ | Clock boost factor $W = 1$ to 40 ⁽⁴⁾ | 5 | — | 800 | 5 | — | 800 | 5 | — | 625 | 5 | — | 525 | MHz |
| $f_{\text{HCLK_in}}$ (input clock frequency) Single Ended I/O Standards | Clock boost factor $W = 1$ to 40 ⁽⁴⁾ | 5 | — | 520 | 5 | — | 520 | 5 | — | 420 | 5 | — | 420 | MHz |
| $f_{\text{HCLK_OUT}}$ (output clock frequency) | — | 5 | — | 800 | 5 | — | 800 | 5 | — | 625 ⁽⁵⁾ | 5 | — | 525 ⁽⁵⁾ | MHz |

Table 36. High-Speed I/O Specifications for Stratix V Devices ^{(1), (2)} (Part 2 of 4)

| Symbol | Conditions | C1 | | | C2, C2L, I2, I2L | | | C3, I3, I3L, I3YY | | | C4,I4 | | | Unit |
|----------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------|-----|-----|------|------------------|-----|------|-------------------|-----|------|-------|-----|------|------|
| | | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max | |
| Transmitter | | | | | | | | | | | | | | |
| True Differential I/O Standards - f _{HSDR} (data rate) | SERDES factor J = 3 to 10 ^{(9), (11), (12), (13), (14), (15), (16)} | (6) | — | 1600 | (6) | — | 1434 | (6) | — | 1250 | (6) | — | 1050 | Mbps |
| | SERDES factor J ≥ 4 LVDS TX with DPA ^{(12), (14), (15), (16)} | (6) | — | 1600 | (6) | — | 1600 | (6) | — | 1600 | (6) | — | 1250 | Mbps |
| | SERDES factor J = 2, uses DDR Registers | (6) | — | (7) | (6) | — | (7) | (6) | — | (7) | (6) | — | (7) | Mbps |
| | SERDES factor J = 1, uses SDR Register | (6) | — | (7) | (6) | — | (7) | (6) | — | (7) | (6) | — | (7) | Mbps |
| Emulated Differential I/O Standards with Three External Output Resistor Networks - f _{HSDR} (data rate) ⁽¹⁰⁾ | SERDES factor J = 4 to 10 ⁽¹⁷⁾ | (6) | — | 1100 | (6) | — | 1100 | (6) | — | 840 | (6) | — | 840 | Mbps |
| t _{x Jitter} - True Differential I/O Standards | Total Jitter for Data Rate 600 Mbps - 1.25 Gbps | — | — | 160 | — | — | 160 | — | — | 160 | — | — | 160 | ps |
| | Total Jitter for Data Rate < 600 Mbps | — | — | 0.1 | — | — | 0.1 | — | — | 0.1 | — | — | 0.1 | UI |
| t _{x Jitter} - Emulated Differential I/O Standards with Three External Output Resistor Network | Total Jitter for Data Rate 600 Mbps - 1.25 Gbps | — | — | 300 | — | — | 300 | — | — | 300 | — | — | 325 | ps |
| | Total Jitter for Data Rate < 600 Mbps | — | — | 0.2 | — | — | 0.2 | — | — | 0.2 | — | — | 0.25 | UI |

Table 42. Memory Output Clock Jitter Specification for Stratix V Devices ⁽¹⁾, (Part 2 of 2) ⁽²⁾, ⁽³⁾

| Clock Network | Parameter | Symbol | C1 | | C2, C2L, I2, I2L | | C3, I3, I3L, I3YY | | C4,I4 | | Unit |
|---------------|------------------------------|-----------------|-------|------|------------------|------|-------------------|-----|-------|-----|------|
| | | | Min | Max | Min | Max | Min | Max | Min | Max | |
| PHY Clock | Clock period jitter | $t_{JIT(per)}$ | -25 | 25 | -25 | 25 | -30 | 30 | -35 | 35 | ps |
| | Cycle-to-cycle period jitter | $t_{JIT(cc)}$ | -50 | 50 | -50 | 50 | -60 | 60 | -70 | 70 | ps |
| | Duty cycle jitter | $t_{JIT(duty)}$ | -37.5 | 37.5 | -37.5 | 37.5 | -45 | 45 | -56 | 56 | ps |

Notes to Table 42:

- (1) The clock jitter specification applies to the memory output clock pins generated using differential signal-splitter and DDIO circuits clocked by a PLL output routed on a PHY, regional, or global clock network as specified. Altera recommends using PHY clock networks whenever possible.
- (2) The clock jitter specification applies to the memory output clock pins clocked by an integer PLL.
- (3) The memory output clock jitter is applicable when an input jitter of 30 ps peak-to-peak is applied with bit error rate (BER) -12, equivalent to 14 sigma.

OCT Calibration Block Specifications

Table 43 lists the OCT calibration block specifications for Stratix V devices.

Table 43. OCT Calibration Block Specifications for Stratix V Devices

| Symbol | Description | Min | Typ | Max | Unit |
|----------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|--------|
| OCTUSRCLK | Clock required by the OCT calibration blocks | — | — | 20 | MHz |
| T_{OCTCAL} | Number of OCTUSRCLK clock cycles required for OCT R_S/R_T calibration | — | 1000 | — | Cycles |
| $T_{OCTSHIFT}$ | Number of OCTUSRCLK clock cycles required for the OCT code to shift out | — | 32 | — | Cycles |
| T_{RS_RT} | Time required between the <code>dyn_term_ctrl</code> and <code>oe</code> signal transitions in a bidirectional I/O buffer to dynamically switch between OCT R_S and R_T (Figure 10) | — | 2.5 | — | ns |

Figure 10 shows the timing diagram for the `oe` and `dyn_term_ctrl` signals.

Figure 10. Timing Diagram for `oe` and `dyn_term_ctrl` Signals

Table 46. JTAG Timing Parameters and Values for Stratix V Devices

| Symbol | Description | Min | Max | Unit |
|------------|------------------------------------------|-----|-------------------|------|
| t_{JPH} | JTAG port hold time | 5 | — | ns |
| t_{JPCO} | JTAG port clock to output | — | 11 ⁽¹⁾ | ns |
| t_{JPZX} | JTAG port high impedance to valid output | — | 14 ⁽¹⁾ | ns |
| t_{JPXZ} | JTAG port valid output to high impedance | — | 14 ⁽¹⁾ | ns |

Notes to Table 46:

- (1) A 1 ns adder is required for each V_{CCIO} voltage step down from 3.0 V. For example, t_{JPCO} = 12 ns if V_{CCIO} of the TDO I/O bank = 2.5 V, or 13 ns if it equals 1.8 V.
- (2) The minimum TCK clock period is 167 ns if VCCBAT is within the range 1.2V-1.5V when you perform the volatile key programming.

Raw Binary File Size

For the POR delay specification, refer to the “POR Delay Specification” section of the “Configuration, Design Security, and Remote System Upgrades in Stratix V Devices”.

Table 47 lists the uncompressed raw binary file (.rbf) sizes for Stratix V devices.

Table 47. Uncompressed .rbf Sizes for Stratix V Devices

| Family | Device | Package | Configuration .rbf Size (bits) | IOCSR .rbf Size (bits) ^{(4), (5)} |
|--------------|--------|------------------------------|--------------------------------|--------------------------------------------|
| Stratix V GX | 5SGXA3 | H35, F40, F35 ⁽²⁾ | 213,798,880 | 562,392 |
| | | H29, F35 ⁽³⁾ | 137,598,880 | 564,504 |
| | 5SGXA4 | — | 213,798,880 | 563,672 |
| | 5SGXA5 | — | 269,979,008 | 562,392 |
| | 5SGXA7 | — | 269,979,008 | 562,392 |
| | 5SGXA9 | — | 342,742,976 | 700,888 |
| | 5SGXAB | — | 342,742,976 | 700,888 |
| | 5SGXB5 | — | 270,528,640 | 584,344 |
| | 5SGXB6 | — | 270,528,640 | 584,344 |
| | 5SGXB9 | — | 342,742,976 | 700,888 |
| | 5SGXBB | — | 342,742,976 | 700,888 |
| Stratix V GT | 5SGTC5 | — | 269,979,008 | 562,392 |
| | 5SGTC7 | — | 269,979,008 | 562,392 |
| Stratix V GS | 5SGSD3 | — | 137,598,880 | 564,504 |
| | 5SGSD4 | F1517 | 213,798,880 | 563,672 |
| | | — | 137,598,880 | 564,504 |
| | 5SGSD5 | — | 213,798,880 | 563,672 |
| | 5SGSD6 | — | 293,441,888 | 565,528 |
| | 5SGSD8 | — | 293,441,888 | 565,528 |

Table 48. Minimum Configuration Time Estimation for Stratix V Devices

| Variant | Member Code | Active Serial ⁽¹⁾ | | | Fast Passive Parallel ⁽²⁾ | | |
|---------|-------------|------------------------------|------------|---------------------|--------------------------------------|------------|---------------------|
| | | Width | DCLK (MHz) | Min Config Time (s) | Width | DCLK (MHz) | Min Config Time (s) |
| GS | D3 | 4 | 100 | 0.344 | 32 | 100 | 0.043 |
| | D4 | 4 | 100 | 0.534 | 32 | 100 | 0.067 |
| | | 4 | 100 | 0.344 | 32 | 100 | 0.043 |
| | D5 | 4 | 100 | 0.534 | 32 | 100 | 0.067 |
| | D6 | 4 | 100 | 0.741 | 32 | 100 | 0.093 |
| | D8 | 4 | 100 | 0.741 | 32 | 100 | 0.093 |
| E | E9 | 4 | 100 | 0.857 | 32 | 100 | 0.107 |
| | EB | 4 | 100 | 0.857 | 32 | 100 | 0.107 |

Notes to Table 48:

(1) DCLK frequency of 100 MHz using external CLKUSR.

(2) Max FPGA FPP bandwidth may exceed bandwidth available from some external storage or control logic.

Fast Passive Parallel Configuration Timing

This section describes the fast passive parallel (FPP) configuration timing parameters for Stratix V devices.

DCLK-to-DATA[] Ratio for FPP Configuration

FPP configuration requires a different DCLK-to-DATA [] ratio when you enable the design security, decompression, or both features. Table 49 lists the DCLK-to-DATA [] ratio for each combination.

Table 49. DCLK-to-DATA[] Ratio ⁽¹⁾ (Part 1 of 2)

| Configuration Scheme | Decompression | Design Security | DCLK-to-DATA[] Ratio |
|----------------------|---------------|-----------------|----------------------|
| FPP ×8 | Disabled | Disabled | 1 |
| | Disabled | Enabled | 1 |
| | Enabled | Disabled | 2 |
| | Enabled | Enabled | 2 |
| FPP ×16 | Disabled | Disabled | 1 |
| | Disabled | Enabled | 2 |
| | Enabled | Disabled | 4 |
| | Enabled | Enabled | 4 |

Table 49. DCLK-to-DATA[] Ratio ⁽¹⁾ (Part 2 of 2)

| Configuration Scheme | Decompression | Design Security | DCLK-to-DATA[] Ratio |
|----------------------|---------------|-----------------|----------------------|
| FPP ×32 | Disabled | Disabled | 1 |
| | Disabled | Enabled | 4 |
| | Enabled | Disabled | 8 |
| | Enabled | Enabled | 8 |

Note to Table 49:

- (1) Depending on the DCLK-to-DATA[] ratio, the host must send a DCLK frequency that is r times the data rate in bytes per second (Bps), or words per second (Wps). For example, in FPP ×16 when the DCLK-to-DATA[] ratio is 2, the DCLK frequency must be 2 times the data rate in Wps. Stratix V devices use the additional clock cycles to decrypt and decompress the configuration data.



If the DCLK-to-DATA[] ratio is greater than 1, at the end of configuration, you can only stop the DCLK (DCLK-to-DATA[] ratio – 1) clock cycles after the last data is latched into the Stratix V device.

Figure 11 shows the configuration interface connections between the Stratix V device and a MAX II or MAX V device for single device configuration.

Figure 11. Single Device FPP Configuration Using an External Host**Notes to Figure 11:**

- (1) Connect the resistor to a supply that provides an acceptable input signal for the Stratix V device. V_{CCPGM} must be high enough to meet the V_{IH} specification of the I/O on the device and the external host. Altera recommends powering up all configuration system I/Os with V_{CCPGM} .
- (2) You can leave the nCEO pin unconnected or use it as a user I/O pin when it does not feed another device's nCE pin.
- (3) The MSEL pin settings vary for different data width, configuration voltage standards, and POR delay. To connect MSEL, refer to the MSEL Pin Settings section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices" chapter.
- (4) If you use FPP ×8, use DATA[7..0]. If you use FPP ×16, use DATA[15..0].

Table 50 lists the timing parameters for Stratix V devices for FPP configuration when the DCLK-to-DATA [] ratio is 1.

Table 50. FPP Timing Parameters for Stratix V Devices ⁽¹⁾

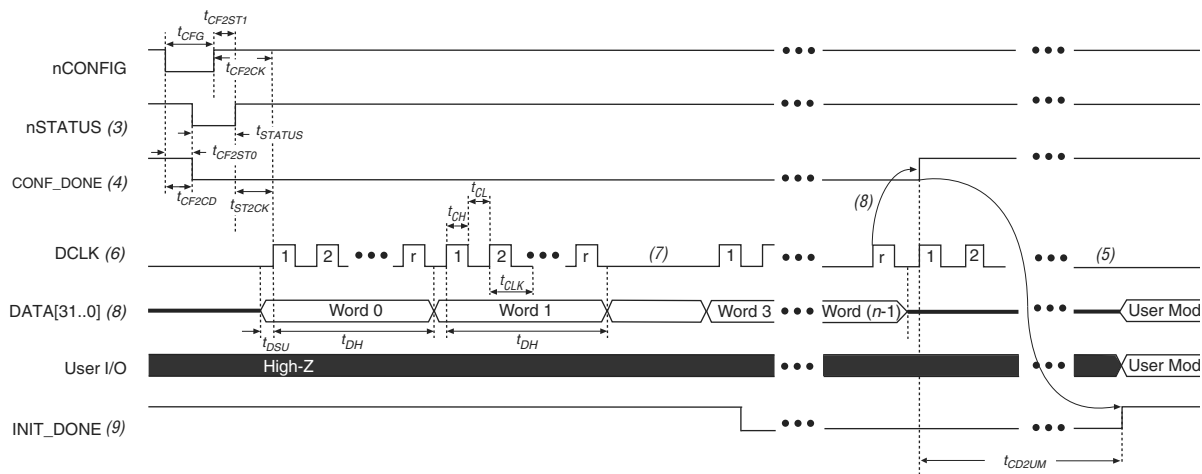
| Symbol | Parameter | Minimum | Maximum | Units |
|-----------------------------------|---------------------------------------------------|-------------------------------------------------------------------|----------------------|-------|
| t _{CF2CD} | nCONFIG low to CONF_DONE low | — | 600 | ns |
| t _{CF2ST0} | nCONFIG low to nSTATUS low | — | 600 | ns |
| t _{CFG} | nCONFIG low pulse width | 2 | — | μs |
| t _{STATUS} | nSTATUS low pulse width | 268 | 1,506 ⁽²⁾ | μs |
| t _{CF2ST1} | nCONFIG high to nSTATUS high | — | 1,506 ⁽³⁾ | μs |
| t _{CF2CK} ⁽⁶⁾ | nCONFIG high to first rising edge on DCLK | 1,506 | — | μs |
| t _{ST2CK} ⁽⁶⁾ | nSTATUS high to first rising edge of DCLK | 2 | — | μs |
| t _{DSU} | DATA [] setup time before rising edge on DCLK | 5.5 | — | ns |
| t _{DH} | DATA [] hold time after rising edge on DCLK | 0 | — | ns |
| t _{CH} | DCLK high time | $0.45 \times 1/f_{\text{MAX}}$ | — | s |
| t _{CL} | DCLK low time | $0.45 \times 1/f_{\text{MAX}}$ | — | s |
| t _{CLK} | DCLK period | $1/f_{\text{MAX}}$ | — | s |
| f _{MAX} | DCLK frequency (FPP $\times 8/\times 16$) | — | 125 | MHz |
| | DCLK frequency (FPP $\times 32$) | — | 100 | MHz |
| t _{CD2UM} | CONF_DONE high to user mode ⁽⁴⁾ | 175 | 437 | μs |
| t _{CD2CU} | CONF_DONE high to CLKUSR enabled | 4 \times maximum DCLK period | — | — |
| t _{CD2UMC} | CONF_DONE high to user mode with CLKUSR option on | t _{CD2CU} + (8576 \times CLKUSR period) ⁽⁵⁾ | — | — |

Notes to Table 50:

- (1) Use these timing parameters when the decompression and design security features are disabled.
- (2) This value is applicable if you do not delay configuration by extending the nCONFIG or nSTATUS low pulse width.
- (3) This value is applicable if you do not delay configuration by externally holding the nSTATUS low.
- (4) The minimum and maximum numbers apply only if you chose the internal oscillator as the clock source for initializing the device.
- (5) To enable the CLKUSR pin as the initialization clock source and to obtain the maximum frequency specification on these pins, refer to the Initialization section of the “Configuration, Design Security, and Remote System Upgrades in Stratix V Devices” chapter.
- (6) If nSTATUS is monitored, follow the t_{ST2CK} specification. If nSTATUS is not monitored, follow the t_{CF2CK} specification.

FPP Configuration Timing when DCLK-to-DATA [] > 1

Figure 13 shows the timing waveform for FPP configuration when using a MAX II device, MAX V device, or microprocessor as an external host. This waveform shows timing when the DCLK-to-DATA [] ratio is more than 1.

Figure 13. FPP Configuration Timing Waveform When the DCLK-to-DATA[] Ratio is >1 (1), (2)**Notes to Figure 13:**

- (1) Use this timing waveform and parameters when the DCLK-to-DATA[] ratio is >1. To find out the DCLK-to-DATA[] ratio for your system, refer to Table 49 on page 55.
- (2) The beginning of this waveform shows the device in user mode. In user mode, nCONFIG, nSTATUS, and CONF_DONE are at logic high levels. When nCONFIG is pulled low, a reconfiguration cycle begins.
- (3) After power-up, the Stratix V device holds nSTATUS low for the time as specified by the POR delay.
- (4) After power-up, before and during configuration, CONF_DONE is low.
- (5) Do not leave DCLK floating after configuration. You can drive it high or low, whichever is more convenient.
- (6) "r" denotes the DCLK-to-DATA[] ratio. For the DCLK-to-DATA[] ratio based on the decompression and the design security feature enable settings, refer to Table 49 on page 55.
- (7) If needed, pause DCLK by holding it low. When DCLK restarts, the external host must provide data on the DATA[31..0] pins prior to sending the first DCLK rising edge.
- (8) To ensure a successful configuration, send the entire configuration data to the Stratix V device. CONF_DONE is released high after the Stratix V device receives all the configuration data successfully. After CONF_DONE goes high, send two additional falling edges on DCLK to begin initialization and enter user mode.
- (9) After the option bit to enable the INIT_DONE pin is configured into the device, the INIT_DONE goes low.

Table 51 lists the timing parameters for Stratix V devices for FPP configuration when the DCLK-to-DATA [] ratio is more than 1.

Table 51. FPP Timing Parameters for Stratix V Devices When the DCLK-to-DATA[] Ratio is >1 ⁽¹⁾

| Symbol | Parameter | Minimum | Maximum | Units |
|----------------------------|---------------------------------------------------|-----------------------------------------------------------------|----------------------|---------|
| t_{CF2CD} | nCONFIG low to CONF_DONE low | — | 600 | ns |
| t_{CF2ST0} | nCONFIG low to nSTATUS low | — | 600 | ns |
| t_{CFG} | nCONFIG low pulse width | 2 | — | μ s |
| t_{STATUS} | nSTATUS low pulse width | 268 | 1,506 ⁽²⁾ | μ s |
| t_{CF2ST1} | nCONFIG high to nSTATUS high | — | 1,506 ⁽²⁾ | μ s |
| t_{CF2CK} ⁽⁵⁾ | nCONFIG high to first rising edge on DCLK | 1,506 | — | μ s |
| t_{ST2CK} ⁽⁵⁾ | nSTATUS high to first rising edge of DCLK | 2 | — | μ s |
| t_{DSU} | DATA [] setup time before rising edge on DCLK | 5.5 | — | ns |
| t_{DH} | DATA [] hold time after rising edge on DCLK | $N-1/f_{DCLK}$ ⁽⁵⁾ | — | s |
| t_{CH} | DCLK high time | $0.45 \times 1/f_{MAX}$ | — | s |
| t_{CL} | DCLK low time | $0.45 \times 1/f_{MAX}$ | — | s |
| t_{CLK} | DCLK period | $1/f_{MAX}$ | — | s |
| f_{MAX} | DCLK frequency (FPP $\times 8/\times 16$) | — | 125 | MHz |
| | DCLK frequency (FPP $\times 32$) | — | 100 | MHz |
| t_R | Input rise time | — | 40 | ns |
| t_F | Input fall time | — | 40 | ns |
| t_{CD2UM} | CONF_DONE high to user mode ⁽³⁾ | 175 | 437 | μ s |
| t_{CD2CU} | CONF_DONE high to CLKUSR enabled | $4 \times$ maximum DCLK period | — | — |
| t_{CD2UMC} | CONF_DONE high to user mode with CLKUSR option on | $t_{CD2CU} + (8576 \times \text{CLKUSR period})$ ⁽⁴⁾ | — | — |

Notes to Table 51:

- (1) Use these timing parameters when you use the decompression and design security features.
- (2) You can obtain this value if you do not delay configuration by extending the nCONFIG or nSTATUS low pulse width.
- (3) The minimum and maximum numbers apply only if you use the internal oscillator as the clock source for initializing the device.
- (4) To enable the CLKUSR pin as the initialization clock source and to obtain the maximum frequency specification on these pins, refer to the Initialization section of the “Configuration, Design Security, and Remote System Upgrades in Stratix V Devices” chapter.
- (5) N is the DCLK-to-DATA ratio and f_{DCLK} is the DCLK frequency the system is operating.
- (6) If nSTATUS is monitored, follow the t_{ST2CK} specification. If nSTATUS is not monitored, follow the t_{CF2CK} specification.

